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**Amendments to the Specification**

Please amend paragraph [0013] on page 5 as follows:

**[0013]** An exemplary method of forming a conductive metal nitride comprising layer using an atomic layer deposition (ALD) method in one preferred embodiment is described in connection with Figs. 1-5. The invention comprises an atomic layer deposition method, although such might be combined with chemical vapor deposition (CVD) or other deposition methods prior to and/or subsequent to an atomic layer deposition method as herein described and claimed. Accordingly, the conductive metal nitride comprising layers which are formed might result from using a combination of the inventive methods disclosed herein with CVD and other methods whether existing or yet-to-be developed. CVD and ALD are used herein as referred to in the co-pending U.S. Patent Application Serial No. 10/133,947, filed on April 25, 2002, entitled "Atomic Layer Deposition Methods and Chemical Vapor Deposition Methods", and listing Brian A. Vaartstra as inventor, and which is now U.S. Publication 20030200917. This ~~10/133,947~~ 20030200917 application is hereby fully incorporated by reference as if presented in its entirety herein.

Please amend paragraph [0014] beginning on page 5 as follows:

[0014] Fig. 1 depicts a substrate 10 comprising some substrate material 12. In the context of this document, the term "semiconductor substrate" or "semiconductive substrate" is defined to mean any construction comprising semiconductive material, including, but not limited to, bulk semiconductive materials such as a semiconductive wafer (either alone or in assemblies comprising other materials thereon), and semiconductive material layers (either alone or in assemblies comprising other materials). The term "substrate" refers to any supporting structure, including, but not limited to, the semiconductive substrates described above. Accordingly, material 12 might constitute one or more materials or layers, including conductive metal nitride comprising layers deposited in accordance with existing, inventive, or yet-to-be develop methods. By way of example only, if a capacitor was being fabricated, the outer surface of material 12 might comprise an insulative layer ~~include~~ including a conductive node over which a capacitor electrode layer comprising a conductive metal nitride would be deposited.